NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **C1-28** is Designed for 28 Volt Class C Amplifier Applications up to 500 MHz.

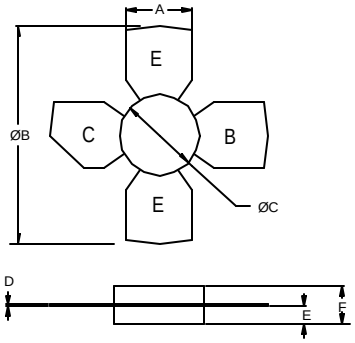
FEATURES:

- P_G = 12 dB Typ. at 1.0 W/400 MHz
- h_C = 65 % Typ. at 1.0 W/400 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	250 mA
V_{CBO}	40 V
V_{CEO}	28 V
V_{EBO}	3.5 V
P_{DISS}	7.0 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
q_{JC}	20 ^{O}C/W

PACKAGE STYLE .280 4L PILL



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.055 / 26.80
C	.275 / 6.99	.285 / 7.24
D	.004 / 0.10	.006 / 0.15
E	.050 / 1.27	.060 . 1.52
F	.118 / 3.00	.130 / 3.30

ORDER CODE: ASI10791

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 5.0 mA	50			V
BV_{CES}	I_C = 5.0 mA	50			V
BV_{EBO}	I_E = 5.0 mA	4.0			V
I_{CBO}	V_{CB} = 28 V			500	mA
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	20		120	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz		3.5`	5.0	pF
P_G h_C	V_{CE} = 28 V P_{OUT} = 1.0 W f = 400 MHz	10 60	12		dB %

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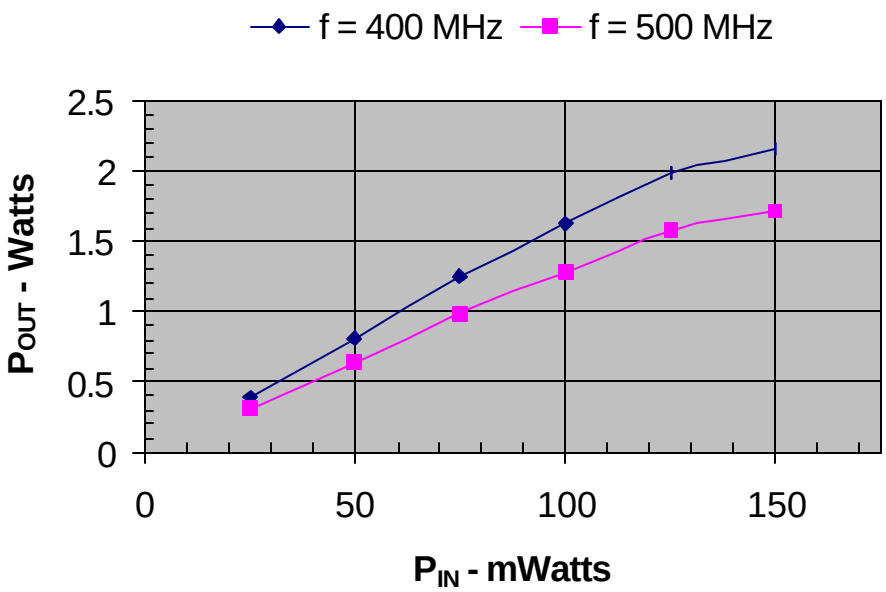
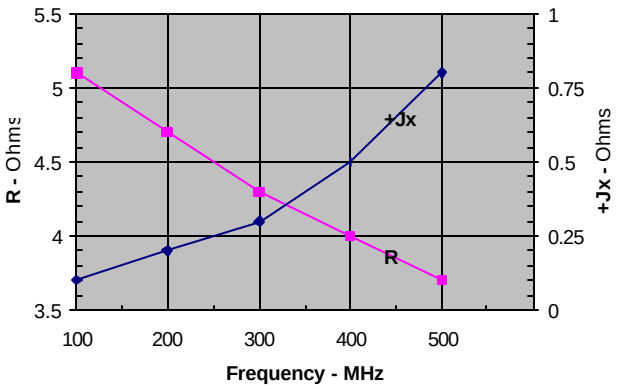
Specifications are subject to change without notice

FOUND.

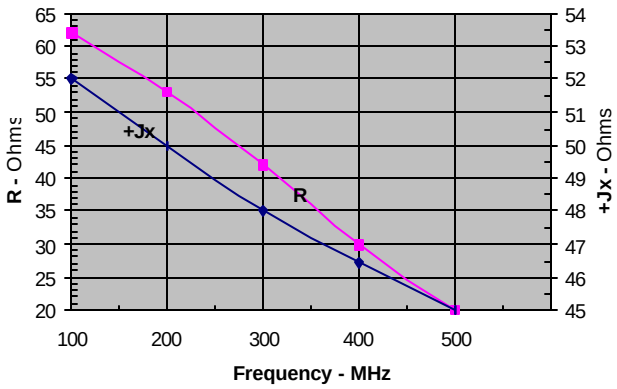
P_{IN} vs. P_{OUT}



Series Input Impedance
R +Jx



Series Load Impedance
R +Jx



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